

ABSTRACT

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This invention provides a memory array and it support signals and a method for byte access for programming, erasing and reading memory cells. The advantage of this array and method is the ability to access bytes for program, erase, and read operations. This array and method uses an added isolation
10 transistor to isolate the high voltage from the unselected byte. In addition, it utilizes a separate source line for each byte in a row. This source line is also shared by a byte in a different row. The array has very little peripheral circuit overhead requirement and it avoids programming disturbances of unselected memory cells.

15